

c) Amendments to the Specification

Please substitute the paragraph beginning at page 3, line 14, and ending at page 4, line 6, with the following replacement paragraph:

--FIG. 2 shows a schematic sectional view of a plasma CVD apparatus as one of representative prior art deposited-film forming apparatuses. With reference to FIG. 2, an example will be described in which an amorphous silicon film is produced by means of a general plasma CVD process using a high frequency. In FIG. 2, reference numeral 1 denotes a plasma processing chamber, reference numeral 2 denotes an exhaust means (a rotary pump and a mechanical booster pump), reference numeral 3 denotes an exhaust line, reference numeral 4 denotes a conductance adjusting valve, reference numeral 5 denotes a power applying electrode, reference numeral 6 denotes a high-frequency power source, reference numeral 7 denotes a high-frequency introducing section, reference numeral 8 denotes a substrate, reference numeral 9 denotes a substrate holder, reference numeral 10 denotes gas introducing section, reference numeral 11 denotes a pressure gauge, reference numeral 12 denotes a discharge region, and reference numeral 15 denotes an exhaust line heater.--